

Silicon PNP Power Transistors

2SB731

DESCRIPTION

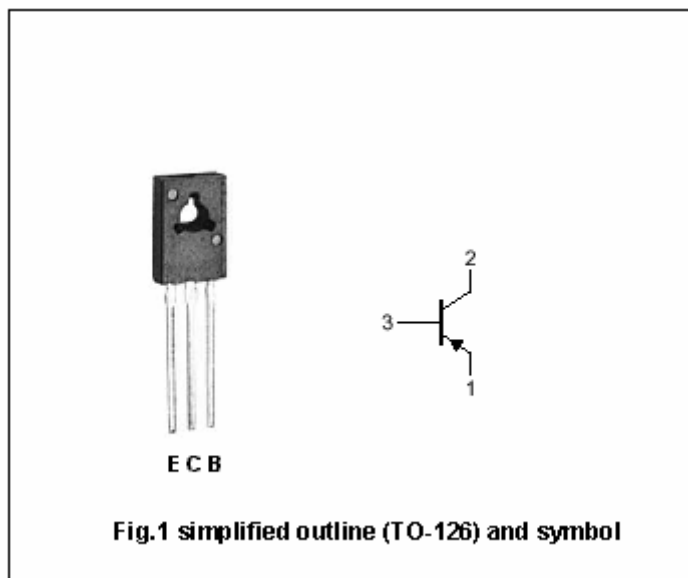
- With TO-126 package
- Complement to type 2SD809
- Low collector saturation voltage

APPLICATIONS

- Audio frequency power amplifier
- Low speed switching

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-60	V
$V_{CEO}$	Collector-emitter voltage	Open base	-50	V
$V_{EBO}$	Emitter-base voltage	Open collector	-6	V
$I_C$	Collector current (DC)		-1	A
$I_{CM}$	Collector current-Peak		-2	A
$I_B$	Base current (DC)		-0.5	A
$P_T$	Total power dissipation	$T_a=25^\circ C$	1.0	W
		$T_C=25^\circ C$	10	
$T_j$	Junction temperature		150	$^\circ C$
$T_{stg}$	Storage temperature		-55~150	$^\circ C$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-1.0A; I <sub>B</sub> =-50mA		-0.5	-0.6	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-1.0A; I <sub>B</sub> =-50mA		-1.0	-1.2	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-50V; I <sub>E</sub> =0			-0.1	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-6V; I <sub>C</sub> =0			-0.1	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-0.1A; V <sub>CE</sub> =-2V	135		600	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-1A; V <sub>CE</sub> =-1V	40			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-10mA; V <sub>CE</sub> =-2V		75		MHz
C <sub>OB</sub>	Collector output capacitance	I <sub>E</sub> =0; f=1MHz; V <sub>CB</sub> =-10V		25		pF

◆ h<sub>FE-1</sub> Classifications

L	K	F	E
135-270	200-400	300-480	360-600

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PACKAGE OUTLINE

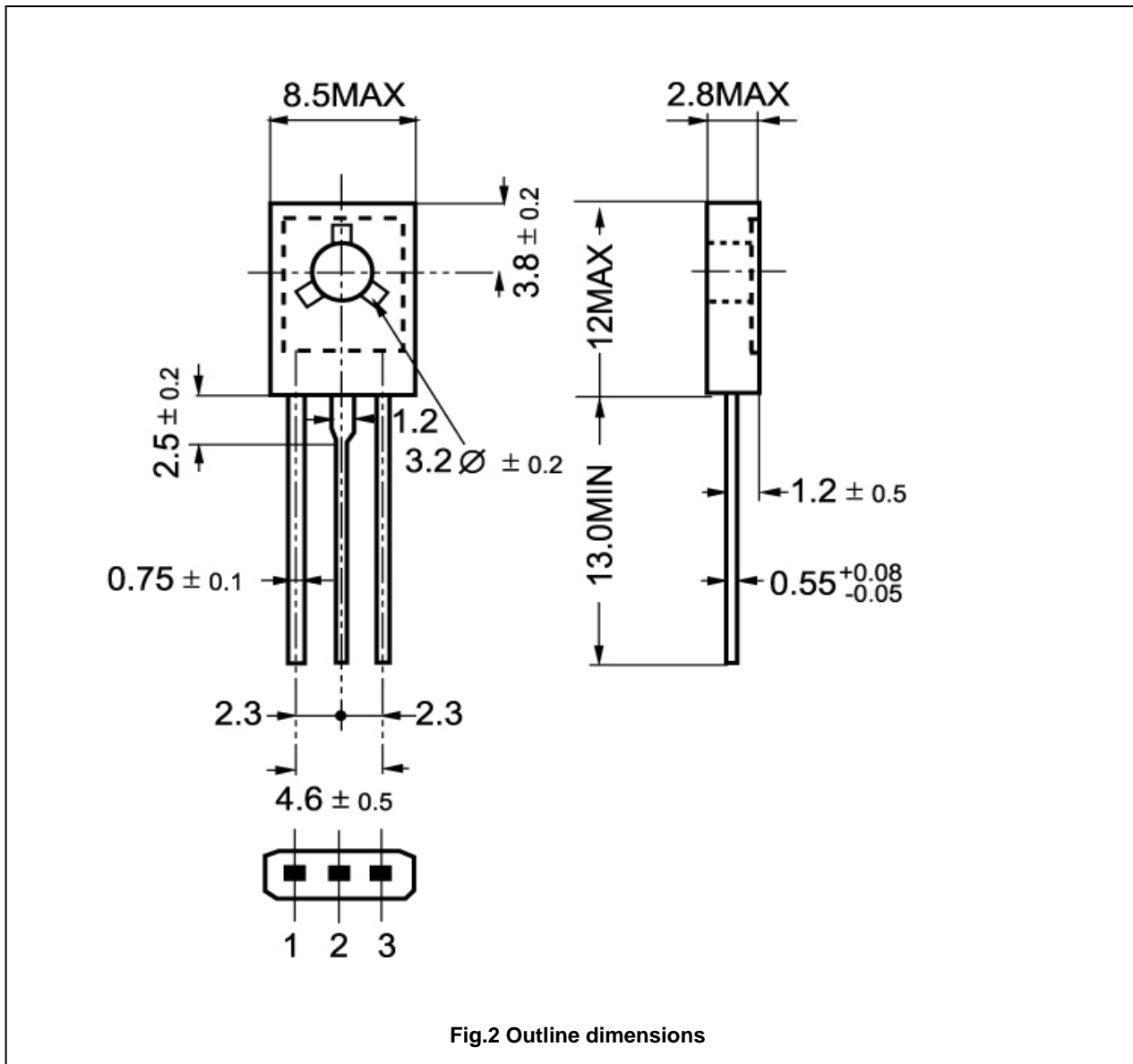


Fig.2 Outline dimensions